NSN 5962-01-341-5886

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View Online at https://aerobasegroup.com/nsn/5962-01-341-5886

Body Length:
1.060 inches
Body Width:
0.310 inches
Body Height:
0.185 inches
Maximum Power Dissipation Rating:
320.0 milliwatts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Ultraviolet erasable and programmed and monolithic and burn in and bidirectional and tested to mil-std-883
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Complementary-metal oxide-semiconductor logic
Input Circuit Pattern:
18 input
Case Outline Source And Designator:
D-8 mil-m-38510
Current Rating Per Characteristic:
80.00 milliamperes reverse current, dc absolute
Terminal Surface Treatment:
Solder
Product Name:
300 gate cmos uv epld
Voltage Rating And Type Per Characteristic:
7.0 volts power source
Capitance Rating Per Characteristic:
12.00 input picofarads
Time Rating Per Chacteristic:
500.00 nanoseconds fall
Memory Device Type:
Pal
Test Data Document:
96906-mil-std 883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:

20 printed circuit

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Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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